



## DUAL EPAD® ULTRA MICROPOWER CMOS OPERATIONAL AMPLIFIER

### KEY FEATURES

- EPAD (Electrically Programmable Analog Device)
- User programmable  $V_{OS}$  trimmer
- Computer-assisted trimming
- Rail-to-rail input/output
- Compatible with standard EPAD Programmer
- Each amplifier  $V_{OS}$  can be trimmed to a different  $V_{OS}$  level
- High precision through in-system circuit precision trimming
- Reduces or eliminates  $V_{OS}$ , PSRR, CMRR and  $TCV_{OS}$  errors
- System level “calibration” capability
- Application Specific Programming mode
- In-System Programming mode
- Electrically programmable to compensate for external component tolerances
- Achieves 0.01pA input bias current and 35 $\mu$ V input offset voltage simultaneously
- $\pm 1V$  to  $\pm 5V$  operation

### GENERAL DESCRIPTION

The ALD2726E/ALD2726 is a dual monolithic rail-to-rail precision CMOS operational amplifier with integrated user programmable EPAD (Electrically Programmable Analog Device) based offset voltage adjustment. The ALD2726E/ALD2726 is a dual version of the ALD1726E/ALD2726 operational amplifier. Each ALD2726E/ALD2726 operational amplifier features individual user-programming offset voltage trimming, resulting in significantly enhanced total system performance and user flexibility. EPAD technology is an exclusive ALD design which has been refined for analog applications where precision voltage trimming is necessary to achieve a desired performance. It utilizes CMOS FETs as in-circuit elements for trimming of offset voltage bias characteristics with the aid of a personal computer under software control. Once programmed, the set parameters are stored indefinitely within the device even after power-down. EPAD offers the circuit designer a convenient and cost-effective trimming solution for achieving the very highest amplifier/system performance.

The ALD2726E/ALD2726 dual operational amplifier features rail-to-rail input and output voltage ranges, tolerance to over-voltage input spikes of 300mV beyond supply rails, capacitive loading up to 25pF, extremely low input currents of 0.01pA typical, high open loop voltage gain, useful bandwidth of 700KHz, slew rate of 0.7V/ $\mu$ s, and low typical supply current of 50 $\mu$ A for both amplifiers.

### ORDERING INFORMATION

Operating Temperature Range		
0°C to +70°C	0°C to +70°C	-55°C to +125°C
14-Pin Small Outline Package (SOIC)	14-Pin Plastic Dip Package	14-Pin CERDIP Package
ALD2726ESB ALD2726SB	ALD2726EPB ALD2726PB	ALD2726EDB ALD2726DB

\* Contact factory for high temperature versions.

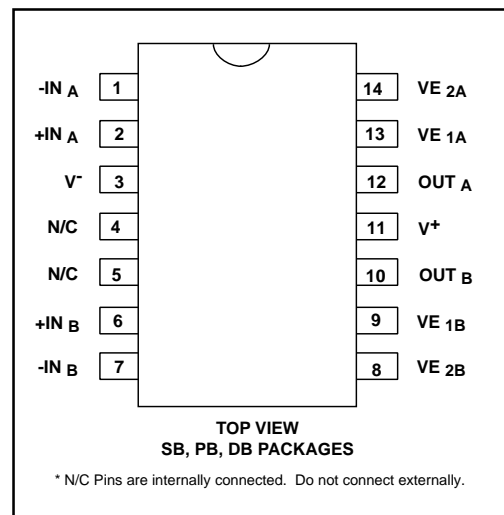
### BENEFITS

- Eliminates manual and elaborate system trimming procedures
- Remote controlled automated trimming
- In-System Programming capability
- No external components
- No internal clocking noise source
- Simple and cost effective
- Small package size
- Extremely small total functional volume size
- Low system implementation cost
- Micropower

### APPLICATIONS

- Sensor interface circuits
- Transducer biasing circuits
- Capacitive and charge integration circuits
- Biochemical probe interface
- Signal conditioning
- Portable instruments
- High source impedance electrode amplifiers
- Precision Sample and Hold amplifiers
- Precision current to voltage converter
- Error correction circuits
- Sensor compensation circuits
- Precision gain amplifiers
- Periodic In-system calibration
- System output level shifter

### PIN CONFIGURATION



## FUNCTIONAL DESCRIPTION

The ALD2726E/ALD2726 uses EPADs as in-circuit elements for trimming of offset voltage bias characteristics. Each ALD2726E/ALD2726 has a pair of EPAD-based circuits connected such that one circuit is used to adjust  $V_{OS}$  in one direction and the other circuit is used to adjust  $V_{OS}$  in the other direction. While each of the EPAD devices is a monotonically adjustable programmable device, the  $V_{OS}$  of the ALD2726E can be adjusted many times in both directions. Once programmed, the set  $V_{OS}$  levels are stored permanently, even when the device power is removed.

### Functional Description of ALD2726E

The ALD2726E is pre-programmed at the factory under standard operating conditions for minimum equivalent input offset voltage. It also has a guaranteed offset voltage program range, which is ideal for applications that require electrical offset voltage programming.

The ALD2726E is an operational amplifier that can be trimmed with user application-specific programming or in-system programming conditions. User application-specific circuit programming refers to the situation where the Total Input Offset Voltage of the ALD2726E can be trimmed with the actual intended operating conditions.

For example, an application circuit may have +1V and -1V power supplies, and the operational amplifier input is biased at +1V, and an average operating temperature at +85°C. The circuit can be wired up to these conditions within an environmental chamber with the ALD2726E inserted into a test socket connected to this circuit while it is being electrically trimmed. Any error in  $V_{OS}$  due to these bias conditions can be automatically zeroed out. The Total  $V_{OS}$  error is now limited only by the adjustable range and the stability of  $V_{OS}$ , and the input noise voltage of the operational amplifier. Therefore, this Total  $V_{OS}$  error now includes  $V_{OS}$  as  $V_{OS}$  is traditionally specified; plus the  $V_{OS}$  error contributions from PSRR, CMRR,  $TCV_{OS}$ , and noise. Typically this total  $V_{OS}$  error ( $V_{OST}$ ) is approximately  $\pm 35\mu V$  for the ALD2726E.

In-System Programming refers to the condition where the EPAD adjustment is made after the ALD2726E has been inserted into a circuit board. In this case, the circuit design must provide for the ALD2726E to operate in normal mode and in programming mode. One of the benefits of in-system programming is that not only is the ALD2726E offset voltage from operating bias conditions accounted for, any residual errors introduced by other circuit components, such as resistor or sensor induced voltage errors, can also be corrected. In this way, the “in-system” circuit output can be adjusted to a desired level, eliminating the need for another trimming function.

## Functional Description of ALD2726

The ALD2726 is pre-programmed at the factory under standard operating conditions for minimum equivalent input offset voltage. The ALD2726 offers similar programmable features as the ALD2726E, but with a more limited offset voltage program range. It is intended for standard operational amplifier applications, where little or no electrical programming by the user is necessary.

### USER PROGRAMMABLE $V_{OS}$ FEATURE

Each ALD2726E/ALD2726 has four additional pins, compared to a conventional dual operational amplifier which has eight pins. These four additional pins are named VE1A, VE2A for op amp A and VE1B, VE2B for op amp B. Each of these pins VE1A, VE2A, VE1B, VE2B (represented by VExx) are connected to a separate, internal offset bias circuit. VExx pins have initial internal bias voltage values of approximately 1V to 2V. The voltage on these pins can be programmed using the ALD E100 EPAD Programmer and the appropriate Adapter Module. The useful programming range of voltages on VExx pins are 1V to 3V.

VExx pins are programming pins, used during electrical programming mode to inject charge into the internal EPADs. Increasing voltage on VE1A/VE1B increases the offset voltage whereas increasing voltage on VE2A/VE2B decreases the offset voltage of op amp A and op amp B, respectively. The injected charge is then permanently stored. After programming, VExx pins must be left open in order for these voltages to remain at the programmed levels.

During programming, voltages on VExx pins are increased incrementally to program the offset voltage of the operational amplifier to the desired  $V_{OS}$ . Note that desired  $V_{OS}$  can be any value within the offset voltage programmable ranges, and can be equal zero, a positive value or a negative value. This  $V_{OS}$  value can also be reprogrammed to a different value at a later time, provided that the useful VE1x or VE2x programming voltage range has not been exceeded. VExx pins can also serve as capacitively coupled input pins.

Internally, VE1 and VE2 are programmed and connected differentially. Temperature drift effects between the two internal offset bias circuits cancel each other and introduce less net temperature drift coefficient change than offset voltage trimming techniques such as offset adjustment with an external trimmer potentiometer.

While programming, V+, VE1 and VE2 pins may be alternately pulsed with 12V (approximately) pulses generated by the EPAD Programmer. In-system programming requires the ALD2726E application circuit to accommodate these programming pulses. This can be accomplished by adding resistors at certain appropriate circuit nodes. For more information, see Application Note AN1700.

## ABSOLUTE MAXIMUM RATINGS

Supply voltage, V+ \_\_\_\_\_ 10.6V  
 Differential input voltage range \_\_\_\_\_ -0.3V to V+ +0.3V  
 Power dissipation \_\_\_\_\_ 600 mW  
 Operating temperature range SB, PB packages \_\_\_\_\_ 0°C to +70°C  
 DB package \_\_\_\_\_ -55°C to +125°C  
 Storage temperature range \_\_\_\_\_ -65°C to +150°C  
 Lead temperature, 10 seconds \_\_\_\_\_ +260°C

**CAUTION:** ESD Sensitive Device. Use static control procedures in ESD controlled environment.

## OPERATING ELECTRICAL CHARACTERISTICS

**T<sub>A</sub> = 25°C V<sub>S</sub> = ±2.5V unless otherwise specified**

Parameter	Symbol	2726E			2726			Unit	Test Conditions
		Min	Typ	Max	Min	Typ	Max		
Supply Voltage	V <sub>S</sub>	±1.0		±5.0	±1.0		±5.0	V	Dual Supply Single Supply
	V+	2.0		10.0	2.0		10.0	V	
Initial Input Offset Voltage <sup>1</sup>	V <sub>OS i</sub>		35	100		50	150	μV	R <sub>S</sub> ≤ 100KΩ
Offset Voltage Program Range <sup>2</sup>	ΔV <sub>OS</sub>	±7	±15		±0.7	±4		mV	
Programmed Input Offset Voltage Error <sup>3</sup>	V <sub>OS</sub>		50	100		50	150	μV	At user specified target offset voltage
Total Input Offset Voltage <sup>4</sup>	V <sub>OST</sub>		50	100		50	150	μV	At user specified target offset voltage
Input Offset Current <sup>5</sup>	I <sub>OS</sub>		0.01	10 240		0.01	10 240	pA pA	T <sub>A</sub> = 25°C 0°C ≤ T <sub>A</sub> ≤ +70°C
Input Bias Current <sup>5</sup>	I <sub>B</sub>		0.01	10 240		0.01	10 240	pA pA	T <sub>A</sub> = 25°C 0°C ≤ T <sub>A</sub> ≤ +70°C
Input Voltage Range <sup>6</sup>	V <sub>IR</sub>	-0.3 -2.8		5.3 +2.8	-0.3 -2.8		5.3 +2.8	V V	V+ = +5V V <sub>S</sub> = ±2.5V
Input Resistance	R <sub>IN</sub>		10 <sup>14</sup>			10 <sup>14</sup>		Ω	
Input Offset Voltage Drift <sup>7</sup>	TCV <sub>OS</sub>		7			7		μV/°C	R <sub>S</sub> ≤ 100KΩ
Initial Power Supply Rejection Ratio <sup>8</sup>	PSRR <sub>i</sub>		90			90		dB	R <sub>S</sub> ≤ 100KΩ
Initial Common Mode Rejection Ratio <sup>8</sup>	CMRR <sub>i</sub>		90			90		dB	R <sub>S</sub> ≤ 100KΩ
Large Signal Voltage Gain	A <sub>V</sub>	15 10	100		15 10	100		V/mV V/mV	R <sub>L</sub> = 100KΩ 0°C ≤ T <sub>A</sub> ≤ +70°C
Output Voltage Range	V <sub>O low</sub> V <sub>O high</sub>	4.99	0.001 4.999	0.01	4.99	0.001 4.999	0.01	V V	R <sub>L</sub> = 1MΩ V = 5V 0°C ≤ T <sub>A</sub> ≤ +70°C
	V <sub>O low</sub> V <sub>O high</sub>	2.40	-2.48 2.48	-2.40	2.40	-2.48 2.48	-2.40	V V	R <sub>L</sub> = 100KΩ 0°C ≤ T <sub>A</sub> ≤ +70°C
Output Short Circuit Current	I <sub>SC</sub>		200			200		μA	

\* NOTES 1 through 9, see section titled "Definitions and Design Notes".

## OPERATING ELECTRICAL CHARACTERISTICS (cont'd)

$T_A = 25^\circ\text{C}$   $V_S = \pm 2.5\text{V}$  unless otherwise specified

Parameter	Symbol	2726E			2726			Unit	Test Conditions
		Min	Typ	Max	Min	Typ	Max		
Supply Current	$I_S$		50	80		50	80	$\mu\text{A}$	$V_{IN} = 0\text{V}$ No Load
Power Dissipation	$P_D$			400			400	mW	$V_S = \pm 2.5\text{V}$
Input Capacitance	$C_{IN}$		1			1		pF	
Maximum Load Capacitance	$C_L$		25			25		pF	
Equivalent Input Noise Voltage	$e_n$		55			55		$\text{nV}/\sqrt{\text{Hz}}$	$f = 1\text{KHz}$
Equivalent Input Noise Current	$i_n$		0.6			0.6		$\text{fA}/\sqrt{\text{Hz}}$	$f = 10\text{Hz}$
Bandwidth	$BW$		200			200		KHz	
Slew Rate	$SR$		0.1			0.1		$\text{V}/\mu\text{s}$	$A_V = +1$ $R_L = 100\text{K}\Omega$
Rise time	$t_r$		1.0			1.0		$\mu\text{s}$	$R_L = 100\text{K}\Omega$
Overshoot Factor			20			20		%	$R_L = 100\text{K}\Omega$ $C_L = 50\text{pF}$
Settling Time	$t_S$		10			10		$\mu\text{s}$	0.1% $A_V = -1$ $R_L = 100\text{K}\Omega$ $C_L = 50\text{pF}$
Channel Separation	$CS$		140			140		dB	$A_V = 100$

$T_A = 25^\circ\text{C}$   $V_S = \pm 2.5\text{V}$  unless otherwise specified

Parameter	Symbol	2726E			2726			Unit	Test Conditions
		Min	Typ	Max	Min	Typ	Max		
Average Long Term Input Offset Voltage Stability <sup>9</sup>	$\frac{\Delta V_{OS}}{\Delta \text{time}}$		0.02			0.02		$\mu\text{V}/1000 \text{ hrs}$	
Initial VE Voltage	$VE1_i, VE2_i$		1.5			1.8		V	
Programmable Change of VE Range	$\Delta VE1, \Delta VE2$	0.5	1.0			0.5		V	
Programmed VE Voltage Error	$e(VE1-VE2)$		0.1			0.1		%	
VE Pin Leakage Current	$i_{eb}$		-5			-5		$\mu\text{A}$	

\* NOTES 1 through 9, see section titled "Definitions and Design Notes".

## OPERATING ELECTRICAL CHARACTERISTICS (cont'd)

$V_S = \pm 2.5V$   $-55^\circ C \leq T_A \leq +125^\circ C$  unless otherwise specified

Parameter	Symbol	2726E			2726			Unit	Test Conditions
		Min	Typ	Max	Min	Typ	Max		
Initial Input offset Voltage	$V_{OSi}$		0.7			0.7		mV	$R_S \leq 100K\Omega$
Input Offset Current	$I_{OS}$			2.0			2.0	nA	
Input Bias Current	$I_B$			2.0			2.0	nA	
Initial Power Supply Rejection Ratio <sup>8</sup>	$PSRR_i$		85			85		dB	$R_S \leq 100K\Omega$
Initial Common Mode Rejection Ratio <sup>8</sup>	$CMRR_i$		83			83		dB	$R_S \leq 100K\Omega$
Large Signal Voltage Gain	$A_V$	15	50		15	50		V/mV	$R_L = 1M\Omega$
Output Voltage Range	$V_{O\ low}$ $V_{O\ high}$	2.35	-2.47 2.45	-2.40	2.35	-2.47 2.45	-2.40	V V	$R_L = 1M\Omega$

$T_A = 25^\circ C$   $V_S = \pm 5.0V$  unless otherwise specified

Parameter	Symbol	2726E			2726			Unit	Test Conditions
		Min	Typ	Max	Min	Typ	Max		
Initial Power Supply Rejection Ratio <sup>8</sup>	$PSRR_i$		80			80		dB	$R_S \leq 100K\Omega$
Initial Common Mode Rejection Ratio <sup>8</sup>	$CMRR_i$		80			80		dB	$R_S \leq 100K\Omega$
Large Signal Voltage Gain	$A_V$		50			50		V/mV	$R_L = 1M\Omega$
Output Voltage Range	$V_{O\ low}$ $V_{O\ high}$	0.9	-0.95 0.95	-0.9	0.9	-0.95 0.95	-0.9	V	$R_L = 1M\Omega$
Bandwidth	BW		0.2			0.2		MHz	
Slew Rate	$S_R$		1.0			1.0		V/ $\mu s$	$A_V = +1, C_L = 25pF$

## DEFINITIONS AND DESIGN NOTES:

1. Initial Input Offset Voltage is the initial offset voltage of the ALD2726E/ALD2726 operational amplifier when shipped from the factory. The device has been pre-programmed and tested for programmability.

2. Offset Voltage Program Range is the range of adjustment of user specified target offset voltage. This is typically an adjustment in either the positive or the negative direction of the input offset voltage from an initial input offset voltage. The input offset programming pins, VE1A/VE1B or VE2A/VE2B, change the input offset voltage in the negative or positive direction, for each of the amplifiers, A or B respectively. User specified target offset voltage can be any offset voltage within this programming range.

3. Programmed Input Offset Voltage Error is the final offset voltage error after programming when the Input Offset Voltage is at target Offset Voltage. This parameter is sample tested.

4. Total Input Offset Voltage is the same as Programmed Input Offset Voltage, corrected for system offset voltage error. Usually this is an all inclusive system offset voltage, which also includes offset voltage contributions from input offset voltage, PSRR, CMRR, TCV<sub>OS</sub> and noise. It can also include errors introduced by external components, at a system level. Programmed Input Offset Voltage and Total Input Offset Voltage is not necessarily zero offset voltage, but an offset voltage set to compensate for other system errors as well. This parameter is sample tested.

5. The Input Offset and Bias Currents are essentially input protection diode reverse bias leakage currents. This low input bias current assures that the analog signal from the source will not be distorted by it. For applications where source impedance is very high, it may be necessary to limit noise and hum pickup through proper shielding.

6. Input Voltage Range is determined by two parallel complementary input stages that are summed internally, each stage having a separate input offset voltage. While Total Input Offset Voltage can be trimmed to a desired target value, it is essential to note that this trimming occurs at only one user selected input bias voltage. Depending on the selected input bias voltage relative to the power supply voltages, offset voltage trimming may affect one or both input stages. For the ALD2726E/ALD2726, the switching point between the two stages occurs at approximately 1.5V below positive supply voltage.

7. Input Offset Voltage Drift is the average change in Total Input Offset Voltage as a function of ambient temperature. This parameter is sample tested.

8. Initial PSRR and initial CMRR specifications are provided as reference information. After programming, error contribution to the offset voltage from PSRR and CMRR is set to zero under the specific power supply and common mode conditions, and becomes part of the Programmed Input Offset Voltage Error.

9. Average Long Term Input Offset Voltage Stability is based on input offset voltage shift through operating life test at 125°C extrapolated to T<sub>A</sub> = 25°C, assuming activation energy of 1.0eV. This parameter is sample tested.

## ADDITIONAL DESIGN NOTES:

A. The ALD2726E/ALD2726 is internally compensated for unity gain stability using a novel scheme which produces a single pole roll off in the gain characteristics while providing more than 70 degrees of phase margin at unity gain frequency. A unity gain buffer using the ALD2726E/ALD2726 will typically drive 25pF of external load capacitance.

B. The ALD2726E/ALD2726 has complementary p-channel and n-channel input differential stages connected in parallel to accomplish rail-to-rail input common mode voltage range. The switching point between the two differential stages is 1.5V below positive supply voltage. For applications such as inverting amplifiers or non-inverting amplifiers with a gain larger than 2.5 (5V operation), the common mode voltage does not make excursions below this switching point. However, this switching does take place if the operational amplifier is connected as a rail-to-rail unity gain buffer and the design must allow for input offset voltage variations.

C. The output stage consists of class AB complementary output drivers. The oscillation resistant feature, combined with the rail-to-rail input and output feature, makes the ALD2726E/ALD2726 an effective analog signal buffer for high source impedance sensors, transducers, and other circuit networks.

D. The ALD2726E/ALD2726 has static discharge protection. However, care must be exercised when handling the device to avoid strong static fields that may degrade a diode junction, causing increased input leakage currents. The user is advised to power up the circuit before, or simultaneously with, any input voltages applied and to limit input voltages not to exceed 0.3V of the power supply voltage levels.

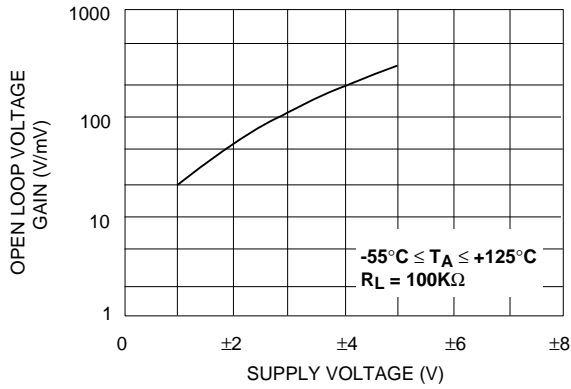
E. V<sub>Exx</sub> are high impedance terminals, as the internal bias currents are set very low to a few microamperes to conserve power. For some applications, these terminals may need to be shielded from external coupling sources. For example, digital signals running nearby may cause unwanted offset voltage fluctuations. Care during the printed circuit board layout, to place ground traces around these pins and to isolate them from digital lines, will generally eliminate such coupling effects. In addition, optional decoupling capacitors of 1000pF or greater value can be added to V<sub>Exx</sub> terminals.

F. The ALD2726E/ALD2726 is designed for use in low voltage, micropower circuits. The maximum operating voltage during normal operation should remain below 10V at all times. Care should be taken to insure that the application in which the device is used does not experience any positive or negative transient voltages that will cause any of the terminal voltages to exceed this limit.

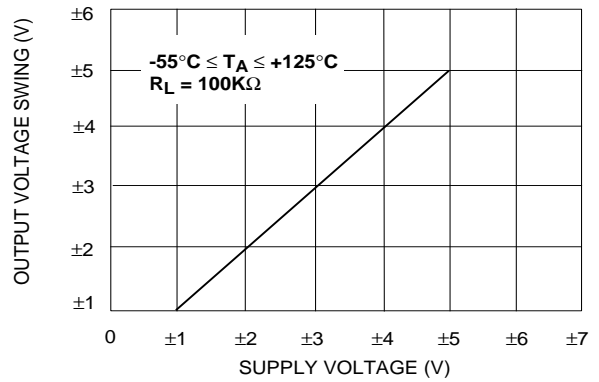
G. All inputs or unused pins except V<sub>Exx</sub> pins should be connected to a supply voltage such as Ground so that they do not become floating pins, since input impedance at these pins is very high. If any of these pins are left undefined, they may cause unwanted oscillation or intermittent excessive current drain. As these devices are built with CMOS technology, normal operating and storage temperature limits, ESD and latchup handling precautions pertaining to CMOS device handling should be observed.

# TYPICAL PERFORMANCE CHARACTERISTICS

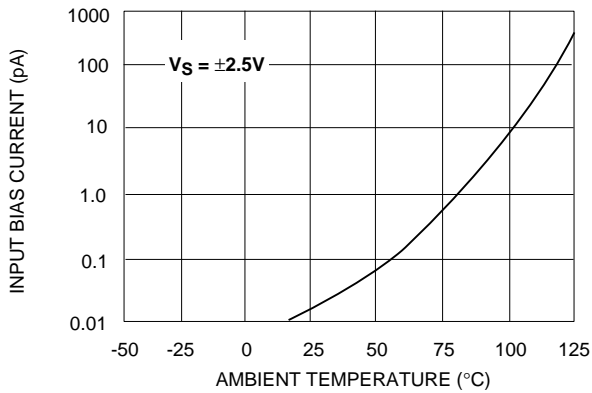
**OPEN LOOP VOLTAGE GAIN AS A FUNCTION OF SUPPLY VOLTAGE AND TEMPERATURE**



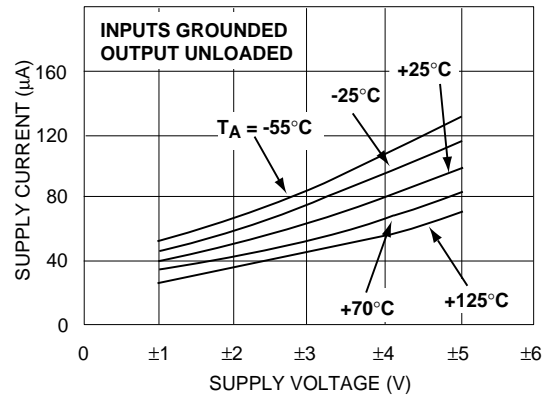
**OUTPUT VOLTAGE SWING AS A FUNCTION OF SUPPLY VOLTAGE**



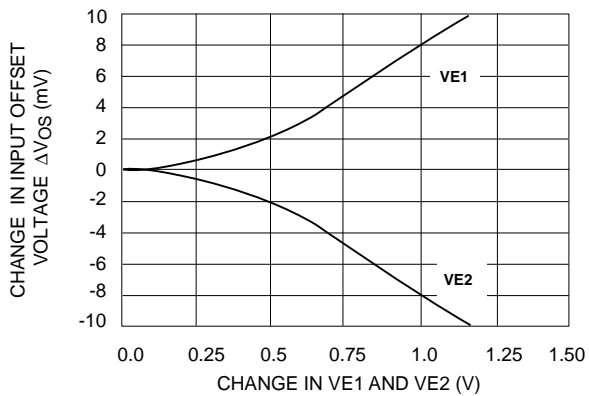
**INPUT BIAS CURRENT AS A FUNCTION OF AMBIENT TEMPERATURE**



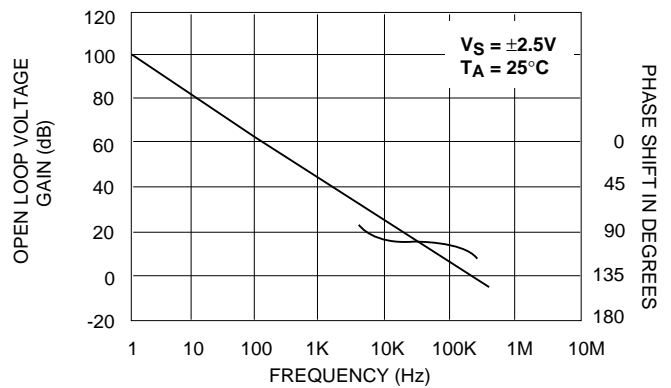
**SUPPLY CURRENT AS A FUNCTION OF SUPPLY VOLTAGE**



**ADJUSTMENT IN INPUT OFFSET VOLTAGE AS A FUNCTION OF CHANGE IN VE1 AND VE2**

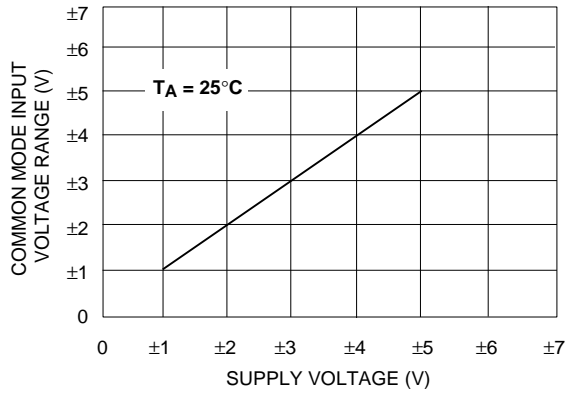


**OPEN LOOP VOLTAGE GAIN AS A FUNCTION OF FREQUENCY**

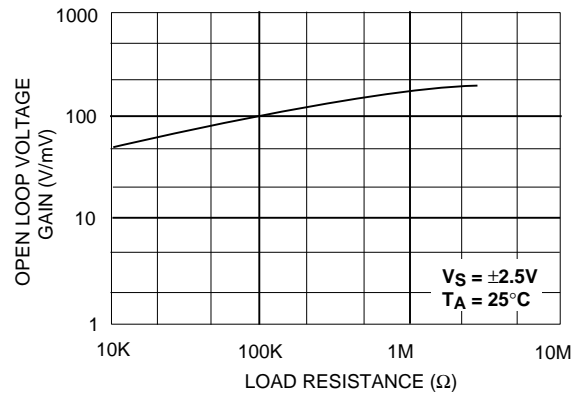


## TYPICAL PERFORMANCE CHARACTERISTICS (cont'd)

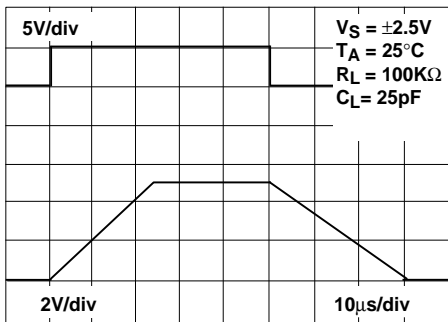
**COMMON MODE INPUT VOLTAGE RANGE AS A FUNCTION OF SUPPLY VOLTAGE**



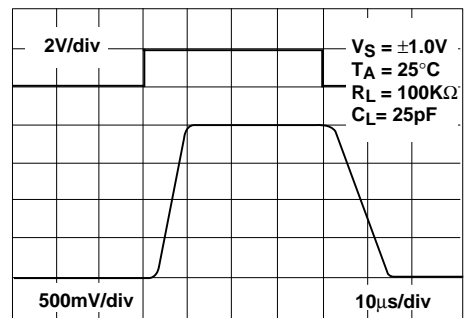
**OPEN LOOP VOLTAGE GAIN AS A FUNCTION OF LOAD RESISTANCE**



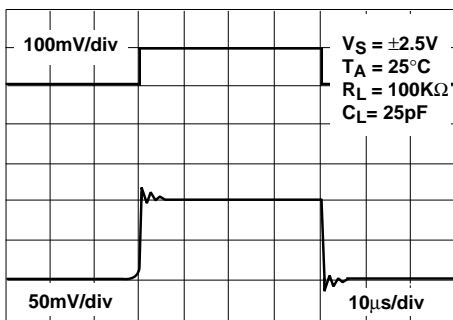
**LARGE - SIGNAL TRANSIENT RESPONSE**



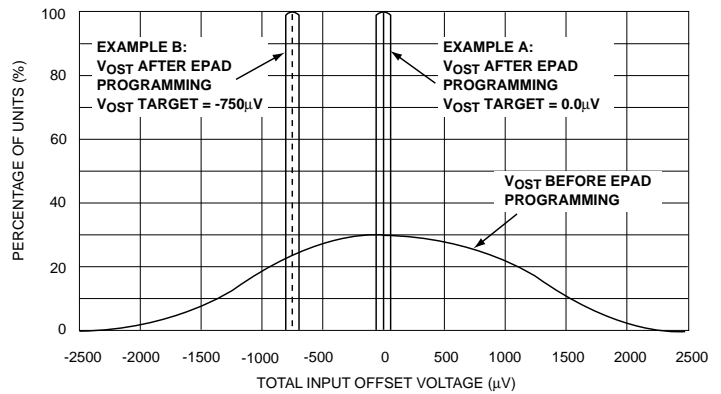
**LARGE - SIGNAL TRANSIENT RESPONSE**



**SMALL - SIGNAL TRANSIENT RESPONSE**

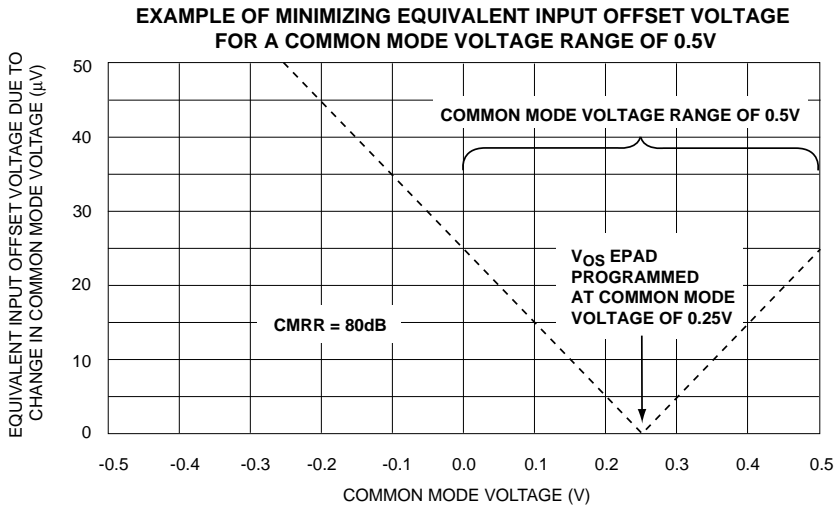
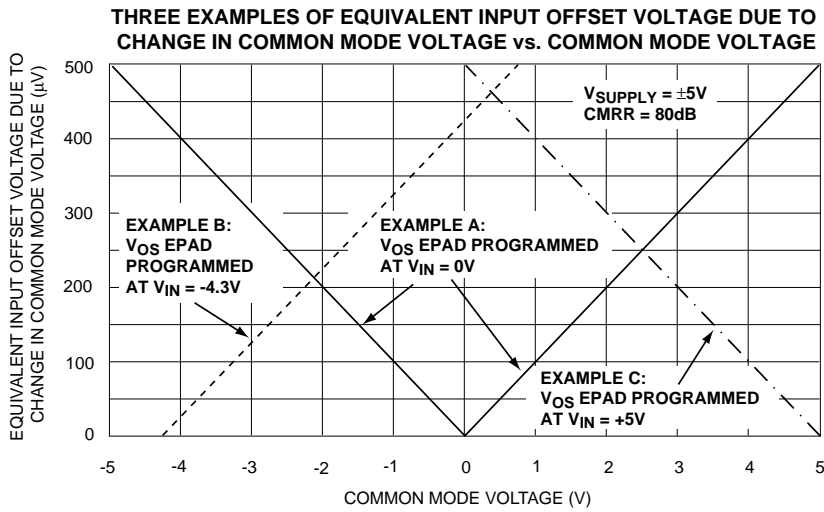
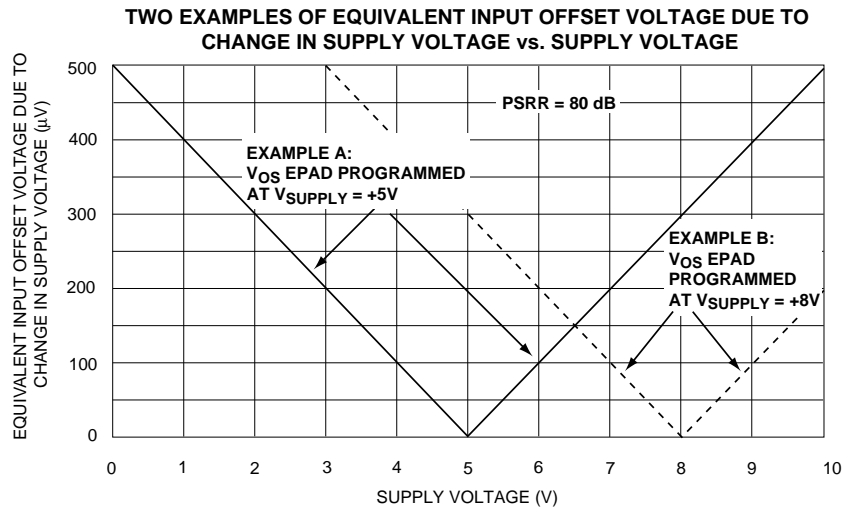


**DISTRIBUTION OF TOTAL INPUT OFFSET VOLTAGE BEFORE AND AFTER EPAD PROGRAMMING**





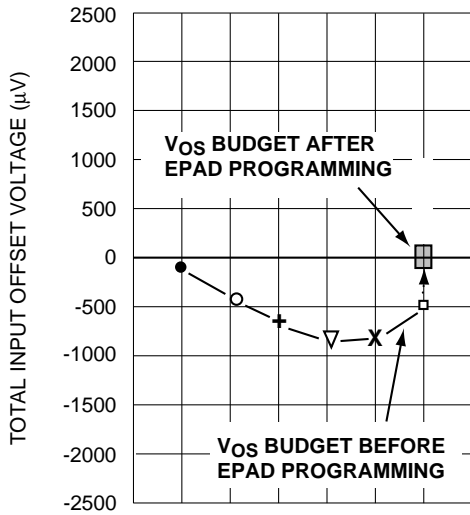
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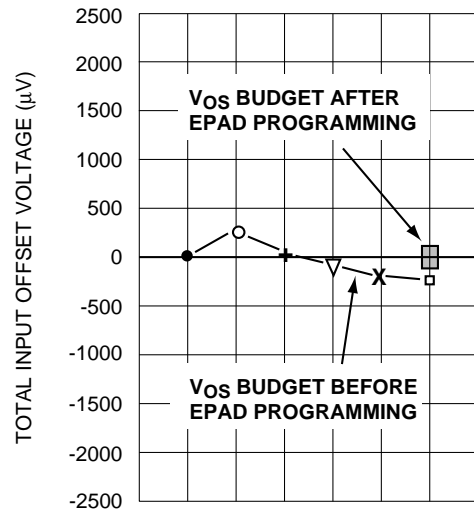
## TYPICAL PERFORMANCE CHARACTERISTICS (cont'd)

### APPLICATION SPECIFIC / IN-SYSTEM PROGRAMMING

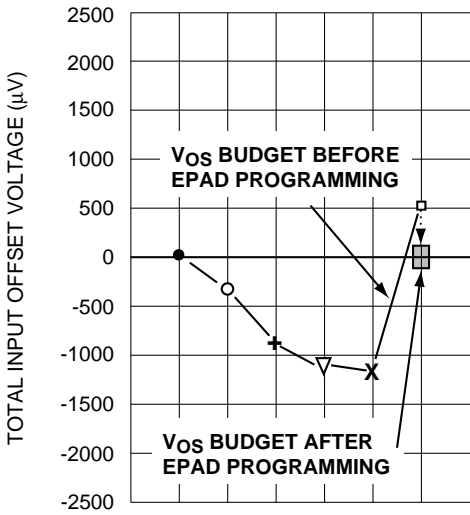
Examples of applications where accumulated total input offset voltage from various contributing sources is minimized under different sets of user-specified operating conditions



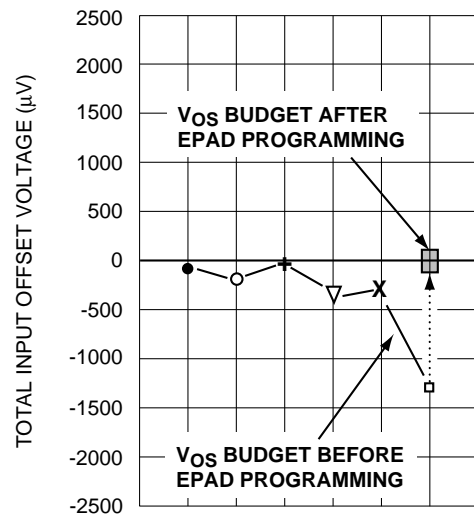
EXAMPLE A



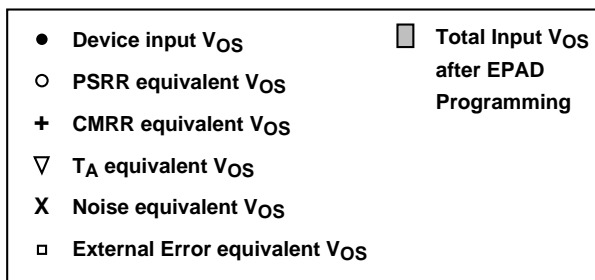
EXAMPLE B



EXAMPLE C

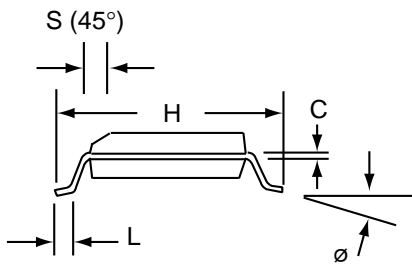
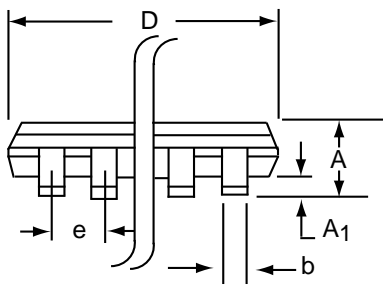
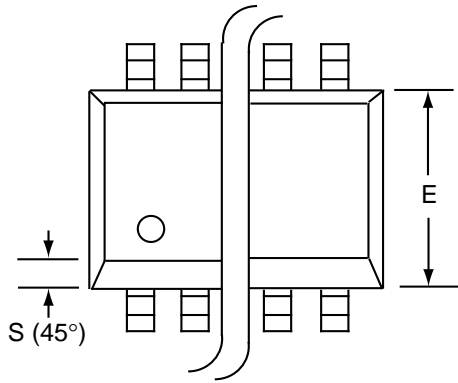


EXAMPLE D



# SOIC-14 PACKAGE DRAWING

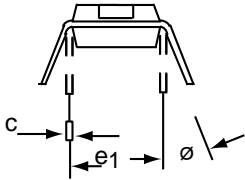
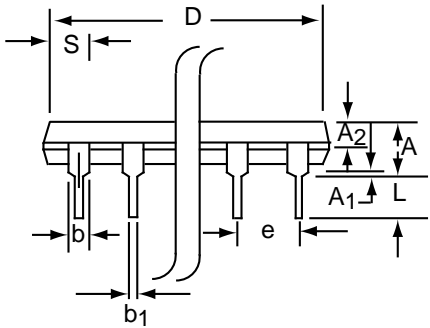
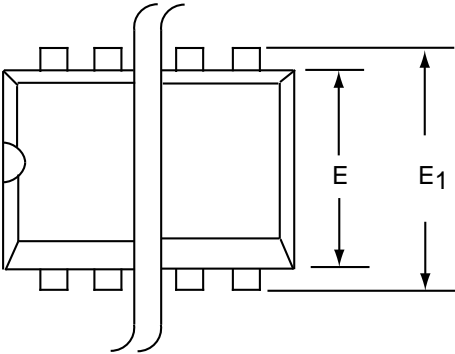
## 14 Pin Plastic SOIC Package



Dim	Millimeters		Inches	
	Min	Max	Min	Max
A	1.35	1.75	0.053	0.069
A <sub>1</sub>	0.10	0.25	0.004	0.010
b	0.35	0.45	0.014	0.018
C	0.18	0.25	0.007	0.010
D-14	8.55	8.75	0.336	0.345
E	3.50	4.05	0.140	0.160
e	1.27 BSC		0.050 BSC	
H	5.70	6.30	0.224	0.248
L	0.60	0.937	0.024	0.037
ø	0°	8°	0°	8°
S	0.25	0.50	0.010	0.020

# PDIP-14 PACKAGE DRAWING

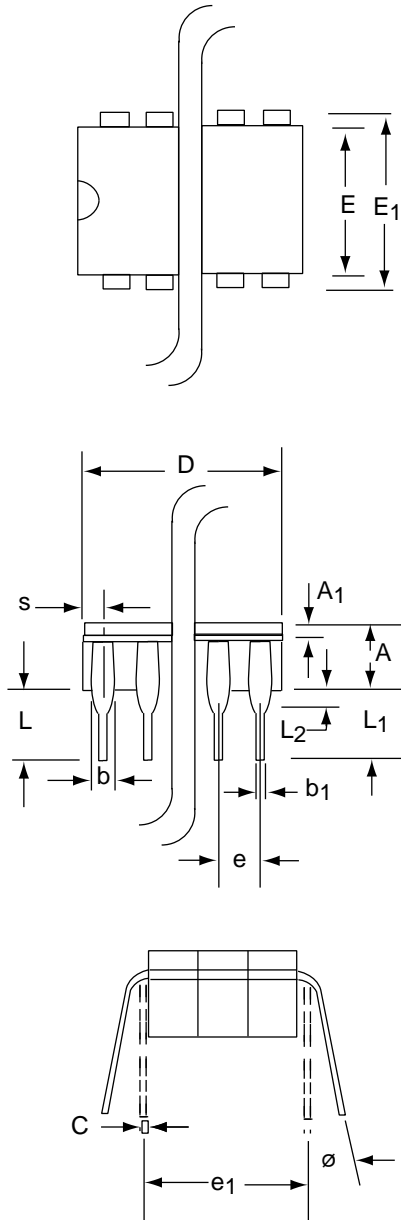
## 14 Pin Plastic DIP Package



Dim	Millimeters		Inches	
	Min	Max	Min	Max
A	3.81	5.08	0.105	0.200
A <sub>1</sub>	0.38	1.27	0.015	0.050
A <sub>2</sub>	1.27	2.03	0.050	0.080
b	0.89	1.65	0.035	0.065
b <sub>1</sub>	0.38	0.51	0.015	0.020
c	0.20	0.30	0.008	0.012
D-14	17.27	19.30	0.680	0.760
E	5.59	7.11	0.220	0.280
E <sub>1</sub>	7.62	8.26	0.300	0.325
e	2.29	2.79	0.090	0.110
e <sub>1</sub>	7.37	7.87	0.290	0.310
L	2.79	3.81	0.110	0.150
S-14	1.02	2.03	0.040	0.080
ø	0°	15°	0°	15°

# CERDIP-14 PACKAGE DRAWING

## 14 Pin CERDIP Package



Dim	Millimeters		Inches	
	Min	Max	Min	Max
A	3.55	5.08	0.140	0.200
A <sub>1</sub>	1.27	2.16	0.050	0.085
b	0.97	1.65	0.038	0.065
b <sub>1</sub>	0.36	0.58	0.014	0.023
C	0.20	0.38	0.008	0.015
D-14	--	19.94	--	0.785
E	5.59	7.87	0.220	0.310
E <sub>1</sub>	7.73	8.26	0.290	0.325
e	2.54 BSC		0.100 BSC	
e <sub>1</sub>	7.62 BSC		0.300 BSC	
L	3.81	5.08	0.150	0.200
L <sub>1</sub>	3.18	--	0.125	--
L <sub>2</sub>	0.38	1.78	0.015	0.070
S	--	2.49	--	0.098
∅	0°	15°	0°	15°